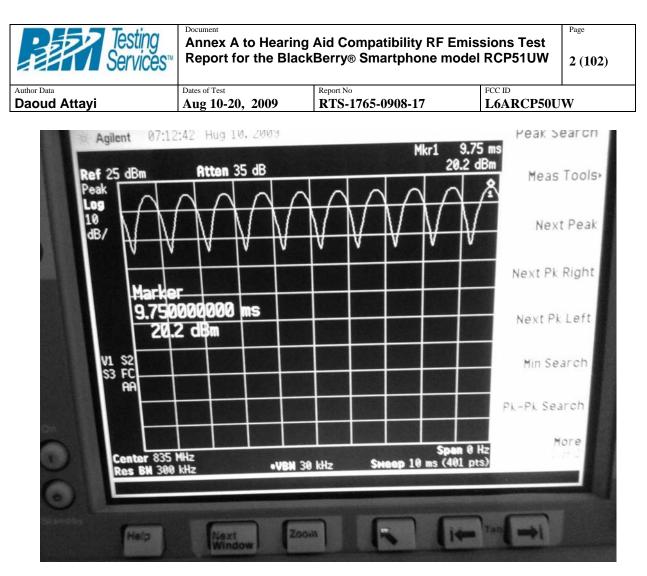
Testing Services <sup>™</sup>	Annex A to Hearin Report for the Blac	Page 1 (102)		
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	Aug 10-20, 2009	RTS-1765-0908-17	L6ARCP50U	W

#### Annex A: Measurement data and plots

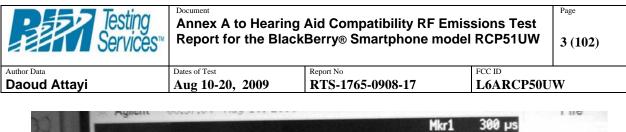
#### A.1 Spectrum analyser plots: CW, 80%AM and GSM signals

Agilen	t 07:09:/	17 Aug 10			Mkr1 2	Peak Search
Ref 25 (	dBm	Atten 35	5 dB		20	1 dBm Meas Tools
Log 10 dB/		1				Next Peak
						Next Pk Right
	Marker 2.3250 20.1	00000 dBm	ns			Next Pk Left
V1 S S3 F						Min Search
A						Pk-Pk Search
	035 MH	-			Span Neep 10 ms (40	0 Hz
Cer Ret	ter 835 MH BN 300 kH	z	•VBN 30	) kHz S	Neep 10 ms (40	
uniday	Help	Next	Z34			- Tat -)
		Windo				

0 Hz Span CW Plot (835MHz)



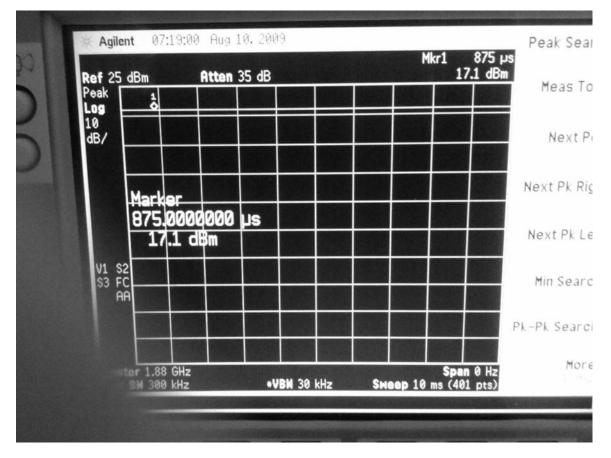
0 Hz Span 80% AM Plot (835MHz)





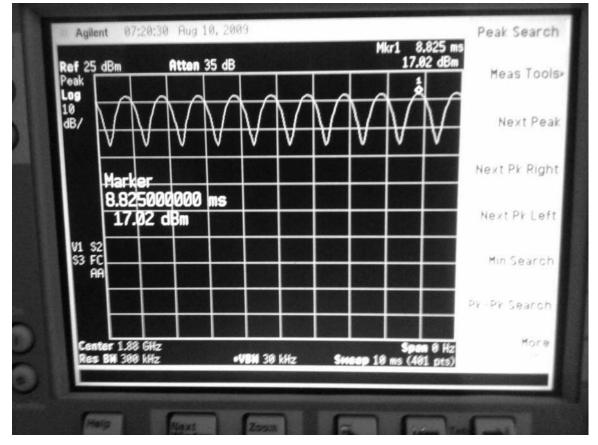
0 Hz Span GSM (835MHz)

Testing Services™	Annex A to Hearing Report for the Black	Page 4 (102)		
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	Aug 10-20, 2009	RTS-1765-0908-17	L6ARCP50U	W



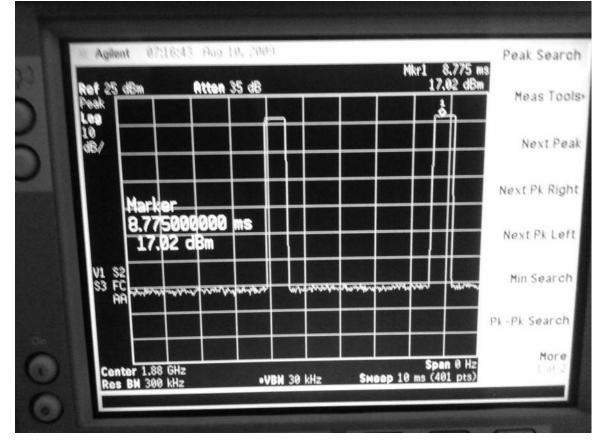
0 Hz Span CW Plot (1880MHz)





0 Hz Span 80% AM Plot (1880MHz)

Testing Services™	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RCP51UW			
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	Aug 10-20, 2009	RTS-1765-0908-17	L6ARCP50U	W



0 Hz Span GSM (1880MHz)

Testing Services <sup>™</sup>	Annex A to Hearing Report for the Black	Page 7 (102)		
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	Aug 10-20, 2009	RTS-1765-0908-17	L6ARCP50U	W

#### A.2 Dipole validation and probe modulation factor plots

Testing Services <sup>™</sup>	Annex A to Hearin Report for the Blac	Page 8 (102)		
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	Aug 10-20, 2009	RTS-1765-0908-17	L6ARCP50U	W

Date/Time: 11/08/2009 9:12:23 AM

Test Laboratory: RTS

File Name: <u>HAC\_E\_Dipole\_CW835\_20.00dBm.da4</u>

# DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified Program Name: HAC RF E Dipole

Communication System: CW; Frequency: 835 MHz; Duty Cycle: 1:1

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 1000$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 08/01/2009

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, -6.30 mm Reference Value = 102.2 V/m; Power Drift = 0.093 dB Maximum value of Total (measured) = 160.7 V/m



## CD835 Dipole = 10mm/Hearing Aid Compatibility Test (41x361x1):

Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 162.8 V/m

Probe Modulation Factor = 1.00

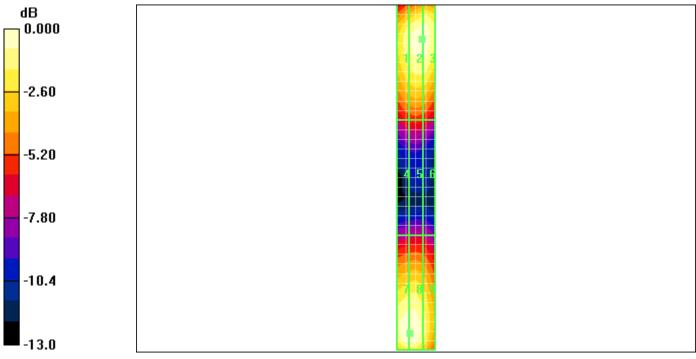
Device Reference Point: 0.000, 0.000, -6.30 mm

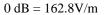
Reference Value = 102.2 V/m; Power Drift = 0.093 dB

#### Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Grid 1	Grid 2	Grid 3
147.2 M4	158.1 M4	158.0 M4
Grid 4	Grid 5	Grid 6
83.4 M4	85.2 M4	83.5 M4
Grid 7	Grid 8	Grid 9
162.6 M4	162.8 M4	142.8 M4

Testing Services™	Annex A to Hearing Report for the Blac	Page 10 (102)			
Author Data	Dates of Test	Report No	FCC ID		
Daoud Attayi	Aug 10-20, 2009	RTS-1765-0908-17	L6ARCP50UW		





This report shall <u>NOT</u> be reproduced except in full without the written consent of RIM Testing Services Copyright 2005-2009, RIM Testing Services, A division of Research In Motion Limited

Testing Services <sup>™</sup>	Annex A to Hearin Report for the Blac	Page 11 (102)		
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	Aug 10-20, 2009	RTS-1765-0908-17	L6ARCP50U	W

Date/Time: 10/08/2009 2:07:16 PM

Test Laboratory: RTS

File Name: <u>HAC\_E\_Dipole\_CW835\_PMF\_GSM.da4</u>

# DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified Program Name: HAC RF E Dipole

Communication System: CW; Frequency: 835 MHz; Duty Cycle: 1:1

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 1000$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 08/01/2009

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, -6.30 mm Reference Value = 115.2 V/m; Power Drift = 0.034 dB Maximum value of Total (measured) = 179.0 V/m



## CD835 Dipole = 10mm/Hearing Aid Compatibility Test (41x361x1):

Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 181.3 V/m

Probe Modulation Factor = 1.00

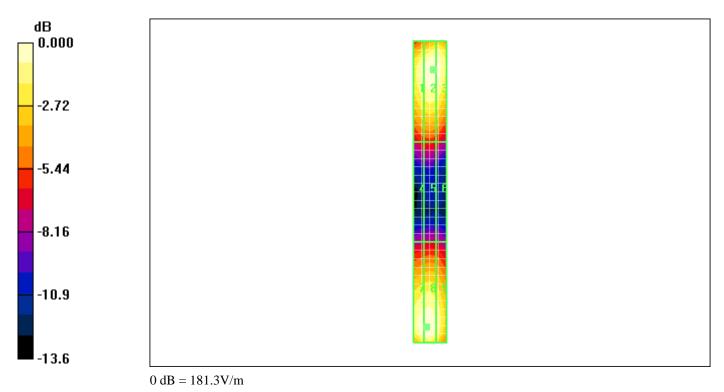
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 115.2 V/m; Power Drift = 0.034 dB

#### Hearing Aid Near-Field Category: M4 (AWF 0 dB)

	,	
Grid 1	Grid 2	Grid 3
170.7 M4	178.6 M4	177.7 M4
Grid 4	Grid 5	Grid 6
90.7 M4	92.7 M4	88.8 M4
Grid 7	Grid 8	Grid 9

Testing Services**	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RCP51UW				
Author Data	Dates of Test	Report No	FCC ID		
Daoud Attayi	Aug 10-20, 2009	RTS-1765-0908-17	L6ARCP50UW		



Testing Services™	Annex A to Hearin Report for the Blac	Page 14 (102)		
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	Aug 10-20, 2009	RTS-1765-0908-17	L6ARCP50U	W

Date/Time: 10/08/2009 2:15:53 PM

Test Laboratory: RTS

File Name: <u>HAC\_E\_Dipole\_AM835\_PMF\_GSM.da4</u>

# DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified Program Name: HAC RF E Dipole

Communication System: CW; Frequency: 835 MHz; Duty Cycle: 1:1

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 1000$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 08/01/2009

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, -6.30 mm Reference Value = 72.9 V/m; Power Drift = -0.076 dB Maximum value of Total (measured) = 112.6 V/m



## CD835 Dipole = 10mm/Hearing Aid Compatibility Test (41x361x1):

Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 113.6 V/m

Probe Modulation Factor = 1.00

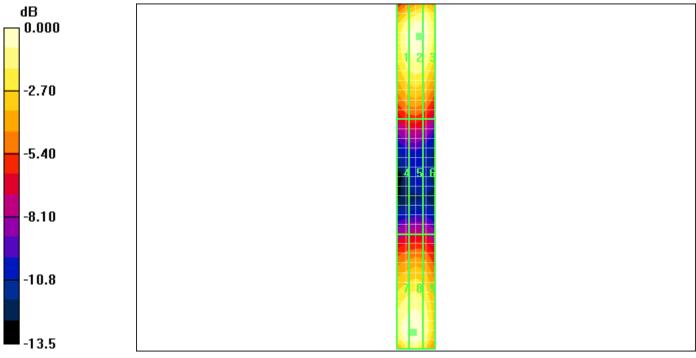
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 72.9 V/m; Power Drift = -0.076 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Grid 1	Grid 2	Grid 3
106.6 M4	110.8 M4	110.3 M4
Grid 4	Grid 5	Grid 6
57.8 M4	58.6 M4	56.5 M4
Grid 7	Grid 8	Grid 9
112.1 M4	113.6 M4	105.3 M4

Testing Services™	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RCP51UW		Page 16 (102)	
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 10-20, 2009 RTS-1765-0908-17 L6ARCP50UW			W



0 dB = 113.6 V/m



Date/Time: 10/08/2009 1:57:31 PM

Test Laboratory: RTS

File Name: HAC\_E\_Dipole\_GSM835.da4

# DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified Program Name: HAC RF E Dipole

Communication System: GSM 850; Frequency: 835 MHz; Duty Cycle: 1:8.3

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 1000$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 08/01/2009

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, -6.30 mm Reference Value = 38.5 V/m; Power Drift = 0.115 dB Maximum value of Total (measured) = 61.9 V/m



## CD835 Dipole = 10mm/Hearing Aid Compatibility Test (41x361x1):

Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 62.4 V/m

Probe Modulation Factor = 1.00

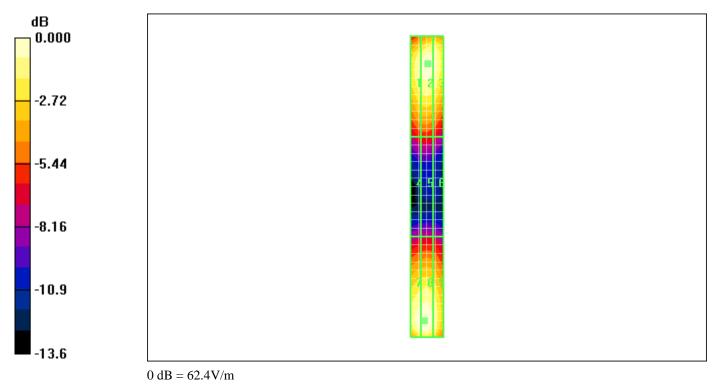
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 38.5 V/m; Power Drift = 0.115 dB

Hearing Aid Near-Field Category: M4 (AWF -5 dB)

Grid 1 Grid 2 Grid 3 57.7 M4 58.7 M4 60.0 M4 Grid 4 Grid 5 Grid 6 31.1 M4 31.3 M4 29.8 M4 Grid 7 Grid 8 Grid 9 61.5 M4 62.4 M4 57.4 M4





Testing Services™	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RCP51UW		Page <b>20 (102)</b>	
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 10-20, 2009 RTS-1765-0908-17 L6ARCP50UV			W

Date/Time: 11/08/2009 9:21:32 AM

Test Laboratory: RTS

File Name: HAC\_E\_Dipole\_CW1880\_20.00dBm.da4

# DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: Not Specified Program Name: HAC RF E Dipole

Communication System: CW; Frequency: 1880 MHz; Duty Cycle: 1:1

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 1000$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 08/01/2009

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid Compatibility Test (5x19x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, -6.30 mm Reference Value = 149.6 V/m; Power Drift = -0.059 dB Maximum value of Total (measured) = 127.9 V/m



## CD1880 Dipole = 10mm/Hearing Aid Compatibility Test (41x181x1):

Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 129.5 V/m

Probe Modulation Factor = 1.00

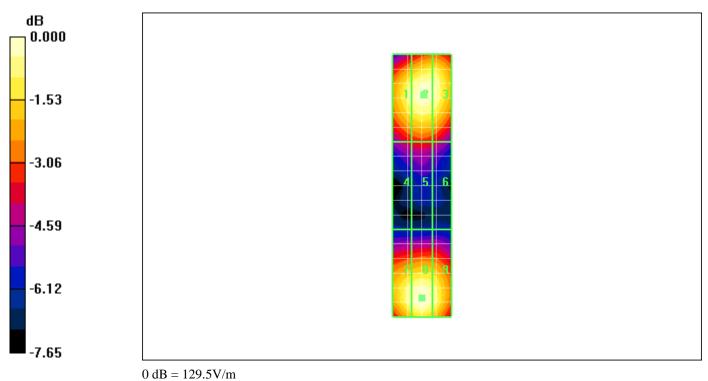
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 149.6 V/m; Power Drift = -0.059 dB

#### Hearing Aid Near-Field Category: M2 (AWF 0 dB)

Grid 1	Grid 2	Grid 3
121.5 M2	126.5 M2	125.1 M2
Grid 4	Grid 5	Grid 6
85.1 M3	88.0 M3	84.9 M3
Grid 7	Grid 8	Grid 9
125.0 M2	129.5 M2	123.9 M2





Testing Services™	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RCP51UW			Page <b>23 (102)</b>
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 10-20, 2009 RTS-1765-0908-17 L6ARCP50UV			W

Date/Time: 10/08/2009 12:04:32 PM

Test Laboratory: RTS

File Name: <u>HAC\_E\_Dipole\_CW1880\_PMF\_GSM.da4</u>

# DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: Not Specified Program Name: HAC RF E Dipole

Communication System: CW; Frequency: 1880 MHz; Duty Cycle: 1:1

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 1000$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 08/01/2009

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid Compatibility Test (5x19x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, -6.30 mm Reference Value = 108.0 V/m; Power Drift = -0.043 dB Maximum value of Total (measured) = 94.2 V/m



## CD1880 Dipole = 10mm/Hearing Aid Compatibility Test (41x181x1):

Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 95.7 V/m

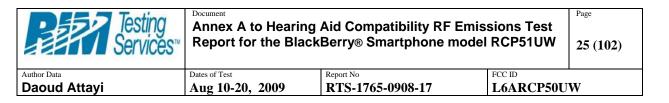
Probe Modulation Factor = 1.00

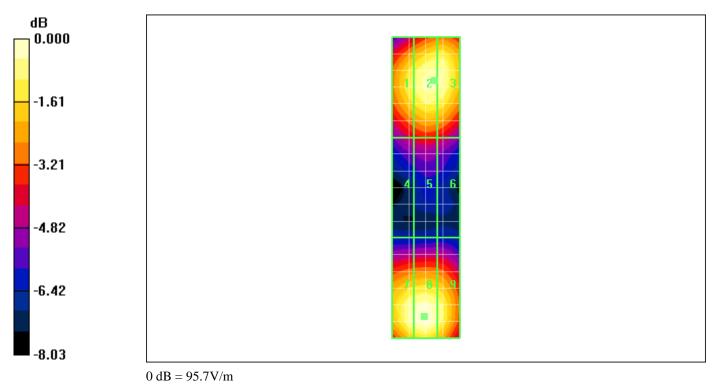
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 108.0 V/m; Power Drift = -0.043 dB

#### Hearing Aid Near-Field Category: M3 (AWF 0 dB)

Grid 1	Grid 2	Grid 3
87.0 M3	92.0 M3	91.8 M3
Grid 4	Grid 5	Grid 6
60.6 M4	63.2 M3	61.3 M4
Grid 7	Grid 8	Grid 9
93.7 M3	95.7 M3	90.7 M3





Testing Services™	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RCP51UW		Page <b>26 (102)</b>	
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 10-20, 2009 RTS-1765-0908-17 L6ARCP50UV			W

Date/Time: 10/08/2009 12:09:30 PM

Test Laboratory: RTS

File Name: <u>HAC\_E\_Dipole\_AM\_1880\_PMF\_GSM.da4</u>

# DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: Not Specified Program Name: HAC RF E Dipole

Communication System: CW; Frequency: 1880 MHz; Duty Cycle: 1:1

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 1000$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 08/01/2009

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid Compatibility Test (5x19x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, -6.30 mm Reference Value = 69.5 V/m; Power Drift = -0.045 dB Maximum value of Total (measured) = 60.3 V/m



## CD1880 Dipole = 10mm/Hearing Aid Compatibility Test (41x181x1):

Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 61.2 V/m

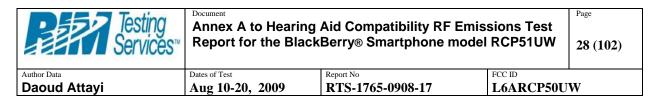
Probe Modulation Factor = 1.00

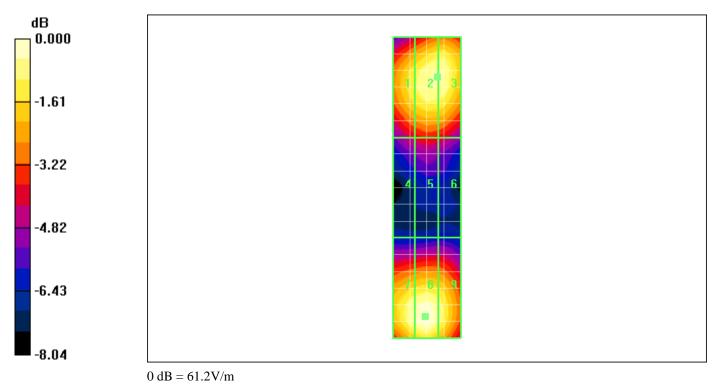
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 69.5 V/m; Power Drift = -0.045 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Grid 1	Grid 2	Grid 3
54.6 M4	58.3 M4	58.3 M4
Grid 4	Grid 5	Grid 6
38.6 M4	40.4 M4	39.3 M4
Grid 7	Grid 8	Grid 9
59.2 M4	61.2 M4	57.4 M4







Date/Time: 10/08/2009 11:48:16 AM

Test Laboratory: RTS

File Name: <u>HAC\_E\_Dipole\_GSM1880.da4</u>

# DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: Not Specified Program Name: HAC RF E Dipole

Communication System: GSM 1900; Frequency: 1880 MHz;Duty Cycle: 1:8.3 Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 1000$  kg/m<sup>3</sup> Phantom section: TCoil Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 08/01/2009

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid Compatibility Test (5x19x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, -6.30 mm Reference Value = 37.7 V/m; Power Drift = -0.035 dB Maximum value of Total (measured) = 32.7 V/m



## CD1880 Dipole = 10mm/Hearing Aid Compatibility Test (41x181x1):

Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 33.2 V/m

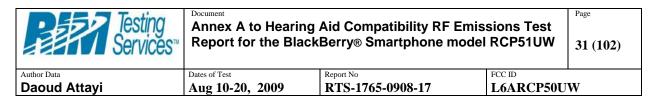
Probe Modulation Factor = 1.00

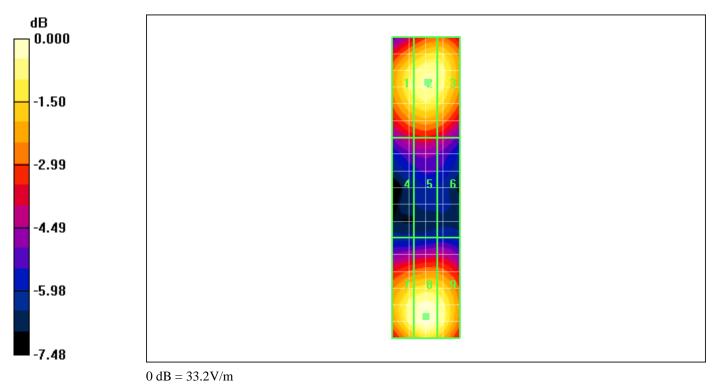
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 37.7 V/m; Power Drift = -0.035 dB

Hearing Aid Near-Field Category: M4 (AWF -5 dB)

Grid 1 Grid 2 Grid 3 30.7 M4 31.7 M4 31.2 M4 Grid 4 Grid 5 Grid 6 21.6 M4 22.2 M4 21.4 M4 Grid 7 Grid 8 Grid 9 33.2 M4 32.2 M4 32.1 M4







Date/Time: 11/08/2009 10:02:03 AM

Test Laboratory: RTS

File Name: HAC\_H\_Dipole\_CW835\_20.00dBm.da4

# DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified Program Name: HAC RF H3DV6 Dipole

Communication System: CW; Frequency: 835 MHz; Duty Cycle: 1:1

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 1$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY4 Configuration:

- Probe: H3DV6 - SN6168; ; Calibrated: 03/03/2009

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x13x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, -6.30 mm Reference Value = 0.475 A/m; Power Drift = 0.081 dB Maximum value of Total (measured) = 0.455 A/m

# H Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (41x121x1):

This report shall <u>NOT</u> be reproduced except in full without the written consent of RIM Testing Services Copyright 2005-2009, RIM Testing Services, A division of Research In Motion Limited



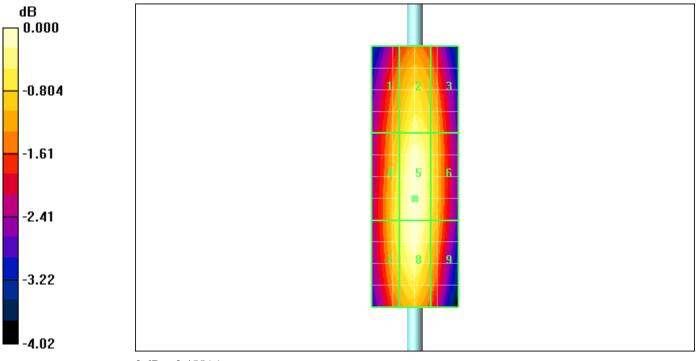
- Measurement grid: dx=5mm, dy=5mm
- Maximum value of peak Total field = 0.455 A/m
- Probe Modulation Factor = 1.00
- Device Reference Point: 0.000, 0.000, -6.30 mm
- Reference Value = 0.475 A/m; Power Drift = 0.081 dB

#### Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak H-field in A/m

Grid 1	Grid 2	Grid 3
0.416 M4	0.435 M4	0.423 M4
Grid 4	Grid 5	Grid 6
0.433 M4	0.455 M4	0.432 M4
Grid 7	Grid 8	Grid 9
0.433 M4	0.454 M4	0.428 M4





0 dB = 0.455 A/m

Testing Services™	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RCP51UW			Page <b>35 (102)</b>
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 10-20, 2009         RTS-1765-0908-17         L6ARCP50UW			W

Date/Time: 11/08/2009 10:08:31 AM

Test Laboratory: RTS

File Name: <u>HAC\_H\_Dipole\_CW835\_PMF\_GSM.da4</u>

# DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified Program Name: HAC RF H3DV6 Dipole

Communication System: CW; Frequency: 835 MHz; Duty Cycle: 1:1

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 1$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY4 Configuration:

- Probe: H3DV6 - SN6168; ; Calibrated: 03/03/2009

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x13x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, -6.30 mm Reference Value = 0.508 A/m; Power Drift = -0.030 dB Maximum value of Total (measured) = 0.477 A/m



## CD835 Dipole = 10mm/Hearing Aid Compatibility Test (41x121x1):

Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.478 A/m

Probe Modulation Factor = 1.00

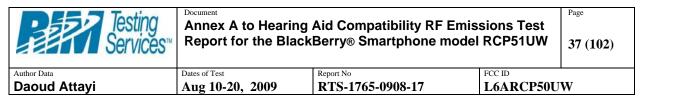
Device Reference Point: 0.000, 0.000, -6.30 mm

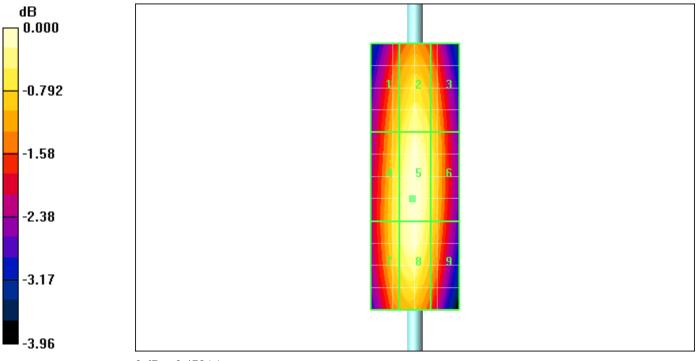
Reference Value = 0.508 A/m; Power Drift = -0.030 dB

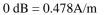
#### Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak H-field in A/m

Grid 1	Grid 2	Grid 3
0.444 M4	0.464 M4	0.448 M4
Grid 4	Grid 5	Grid 6
0.460 M4	0.478 M4	0.455 M4
Grid 7	Grid 8	Grid 9
0.460 M4	0.475 M4	0.449 M4







Testing Services™	Document Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RCP51UW			Page 38 (102)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	Aug 10-20, 2009	RTS-1765-0908-17	L6ARCP50U	W

Date/Time: 11/08/2009 10:19:09 AM

Test Laboratory: RTS

File Name: <u>HAC\_H\_Dipole\_AM835\_PMF\_GSM.da4</u>

# DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified Program Name: HAC RF H3DV6 Dipole

Communication System: CW; Frequency: 835 MHz; Duty Cycle: 1:1

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 1$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY4 Configuration:

- Probe: H3DV6 - SN6168; ; Calibrated: 03/03/2009

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x13x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, -6.30 mm Reference Value = 0.343 A/m; Power Drift = 0.025 dB Maximum value of Total (measured) = 0.322 A/m



### CD835 Dipole = 10mm/Hearing Aid Compatibility Test (41x121x1):

Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.322 A/m

Probe Modulation Factor = 1.00

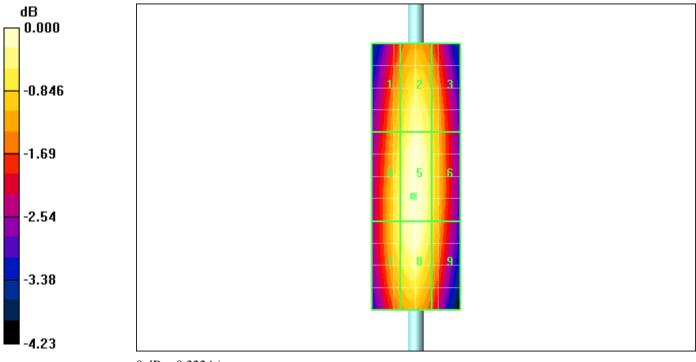
Device Reference Point: 0.000, 0.000, -6.30 mm

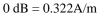
Reference Value = 0.343 A/m; Power Drift = 0.025 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Grid 1	Grid 2	Grid 3
0.298 M4	0.314 M4	0.300 M4
Grid 4	Grid 5	Grid 6
0.309 M4	0.322 M4	0.305 M4
Grid 7	Grid 8	Grid 9
0.309 M4	0.321 M4	0.301 M4









Date/Time: 11/08/2009 10:48:18 AM

Test Laboratory: RTS

File Name: HAC\_H\_Dipole\_GSM835.da4

# DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified Program Name: HAC RF H3DV6 Dipole

Communication System: GSM 850; Frequency: 835 MHz; Duty Cycle: 1:8.3

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 1$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY4 Configuration:

- Probe: H3DV6 - SN6168; ; Calibrated: 03/03/2009

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x13x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, -6.30 mm Reference Value = 0.192 A/m; Power Drift = 0.021 dB Maximum value of Total (measured) = 0.180 A/m



### CD835 Dipole = 10mm/Hearing Aid Compatibility Test (41x121x1):

Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.180 A/m

Probe Modulation Factor = 1.00

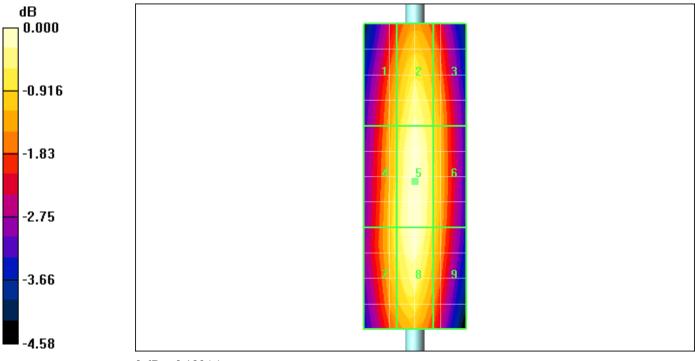
Device Reference Point: 0.000, 0.000, -6.30 mm

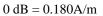
Reference Value = 0.192 A/m; Power Drift = 0.021 dB

Hearing Aid Near-Field Category: M4 (AWF -5 dB)

Grid 1	Grid 2	Grid 3
0.164 M4	0.175 M4	0.167 M4
Grid 4	Grid 5	Grid 6
0.170 M4	0.180 M4	0.169 M4
Grid 7	Grid 8	Grid 9
0.170 M4	0.179 M4	0.166 M4







Testing Services™	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RCP51UW			Page 44 (102)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	Aug 10-20, 2009	RTS-1765-0908-17	L6ARCP50U	W

Date/Time: 11/08/2009 11:47:11 AM

Test Laboratory: RTS

File Name: HAC\_H\_Dipole\_CW1880\_20.00dBm.da4

# DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: Not Specified Program Name: HAC RF H3DV6 Dipole

Communication System: CW; Frequency: 1880 MHz; Duty Cycle: 1:1

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 1$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY4 Configuration:

- Probe: H3DV6 - SN6168; ; Calibrated: 03/03/2009

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x13x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, -6.30 mm Reference Value = 0.493 A/m; Power Drift = -0.077 dB Maximum value of Total (measured) = 0.451 A/m



### CD835 Dipole = 10mm/Hearing Aid Compatibility Test (41x121x1):

Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.451 A/m

Probe Modulation Factor = 1.00

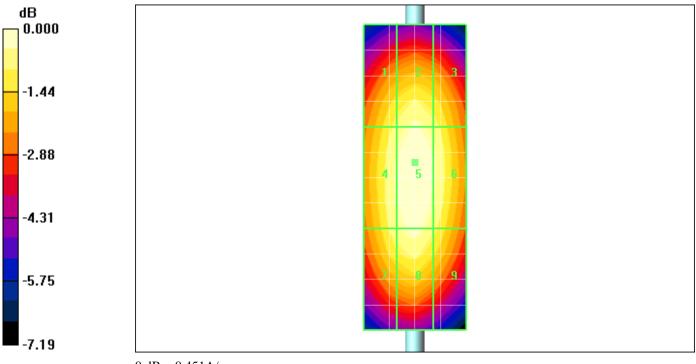
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.493 A/m; Power Drift = -0.077 dB

Hearing Aid Near-Field Category: M2 (AWF 0 dB)

Grid 1 Grid 2 Grid 3 0.415 M2 0.433 M2 0.418 M2 Grid 4 Grid 6 Grid 5 0.433 M2 0.451 M2 0.435 M2 Grid 7 Grid 8 Grid 9 0.415 M2 0.422 M2 0.436 M2





 $0 \, dB = 0.451 \text{A/m}$ 

Testing Services™	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RCP51UW			Page 47 (102)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	Aug 10-20, 2009	RTS-1765-0908-17	L6ARCP50U	W

Date/Time: 11/08/2009 11:51:04 AM

Test Laboratory: RTS

File Name: <u>HAC\_H\_Dipole\_CW1880\_PMF\_GSM.da4</u>

# DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: Not Specified Program Name: HAC RF H3DV6 Dipole

Communication System: CW; Frequency: 1880 MHz; Duty Cycle: 1:1

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 1$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY4 Configuration:

- Probe: H3DV6 - SN6168; ; Calibrated: 03/03/2009

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x13x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, -6.30 mm Reference Value = 0.334 A/m; Power Drift = 0.122 dB Maximum value of Total (measured) = 0.317 A/m



### CD835 Dipole = 10mm/Hearing Aid Compatibility Test (41x121x1):

Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.317 A/m

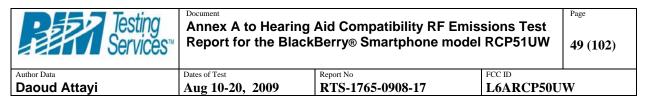
Probe Modulation Factor = 1.00

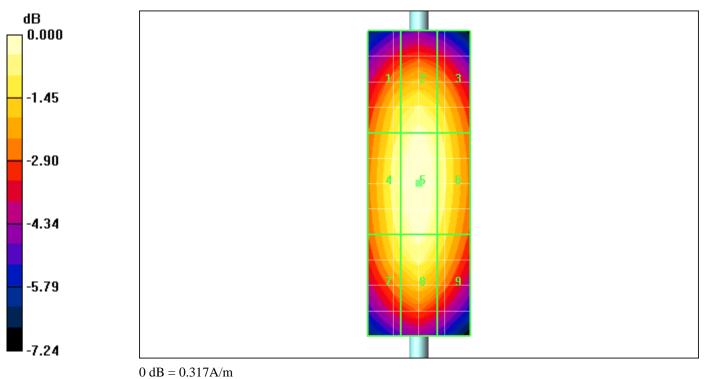
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.334 A/m; Power Drift = 0.122 dB

Hearing Aid Near-Field Category: M3 (AWF 0 dB)

Grid 1	Grid 2	Grid 3
0.291 M3	0.305 M3	0.291 M3
Grid 4	Grid 5	Grid 6
0.304 M3	0.317 M3	0.301 M3
Grid 7	Grid 8	Grid 9
0.293 M3	0.306 M3	0.287 M3







Date/Time: 11/08/2009 12:05:51 PM

Test Laboratory: RTS

File Name: HAC\_H\_Dipole\_AM1880\_PMF\_GSM.da4

## DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: Not Specified Program Name: HAC RF H3DV6 Dipole

Communication System: AM 80%; Frequency: 1880 MHz; Duty Cycle: 1:1

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 1$  kg/m<sup>3</sup>

Phantom section: TCoil Section

DASY4 Configuration:

- Probe: H3DV6 - SN6168; ; Calibrated: 03/03/2009

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid Compatibility Test (5x19x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, -6.30 mm Reference Value = 0.221 A/m; Power Drift = 0.058 dB Maximum value of Total (measured) = 0.206 A/m



### CD1880 Dipole = 10mm/Hearing Aid Compatibility Test (41x181x1):

Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.207 A/m

Probe Modulation Factor = 1.00

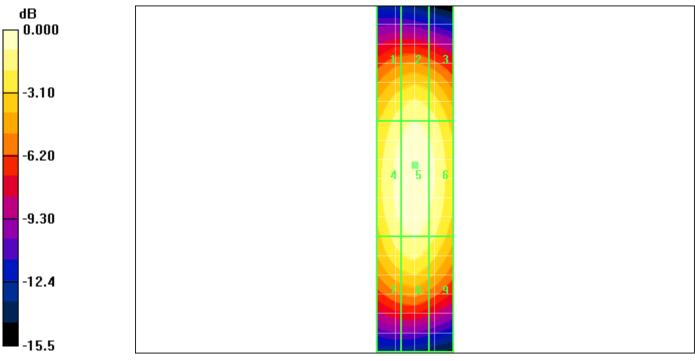
Device Reference Point: 0.000, 0.000, -6.30 mm

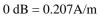
Reference Value = 0.221 A/m; Power Drift = 0.058 dB

Hearing Aid Near-Field Category: M3 (AWF 0 dB)

Grid 1	Grid 2	Grid 3
0.176 M4	0.185 M4	0.176 M4
Grid 4	Grid 5	Grid 6
0.196 M3	0.207 M3	0.194 M3
Grid 7	Grid 8	Grid 9
0.179 M4	0.187 M4	0.173 M4









Date/Time: 11/08/2009 11:28:13 AM

Test Laboratory: RTS

File Name: HAC\_H\_Dipole\_GSM1880.da4

# DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: Not Specified Program Name: HAC RF H3DV6 Dipole

Communication System: GSM 1900; Frequency: 1880 MHz; Duty Cycle: 1:8.3

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 1$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY4 Configuration:

- Probe: H3DV6 - SN6168; ; Calibrated: 03/03/2009

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x13x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, -6.30 mm Reference Value = 0.151 A/m; Power Drift = -0.003 dB Maximum value of Total (measured) = 0.141 A/m



### CD835 Dipole = 10mm/Hearing Aid Compatibility Test (41x121x1):

Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.141 A/m

Probe Modulation Factor = 1.00

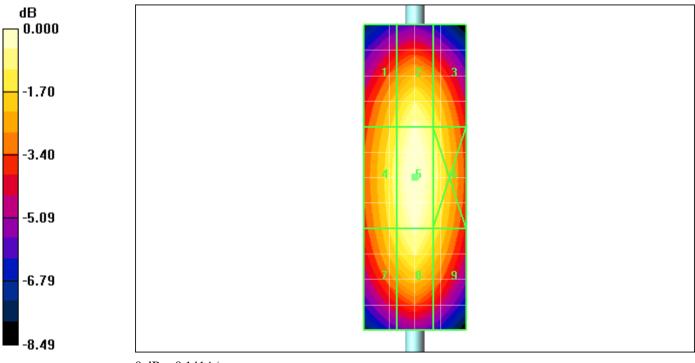
Device Reference Point: 0.000, 0.000, -6.30 mm

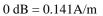
Reference Value = 0.151 A/m; Power Drift = -0.003 dB

Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Grid 1	Grid 2	Grid 3
0.122 M4	0.134 M4	0.124 M4
Grid 4	Grid 5	Grid 6
0.129 M4	0.141 M3	0.130 M4
Grid 7	Grid 8	Grid 9
0.124 M4	0.134 M4	0.123 M4



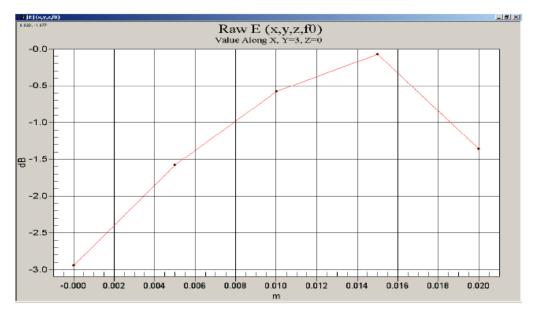




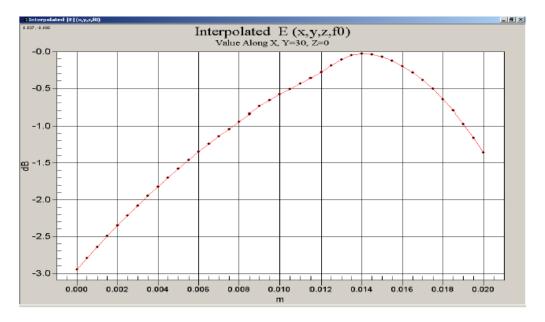
Testing Services™	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RCP51UW			Page <b>56 (102)</b>
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 10-20, 2009			

### Justification of Step Size and Interpolation

This section demonstrates that a 5mm step size with interpolation provides sufficient resolution for RF emissions measurements. The DASY 4 uses interpolation algorithms to derive 9 interpolated points between every measured point.

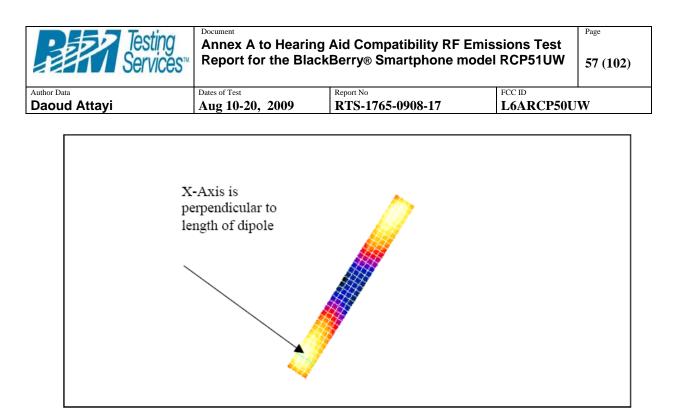


The figure above shows the raw measured field strength perpendicular to the length of the validation dipole. The TCB guidance slides require the 3dB width to be much larger than the step size. The width between -3dB points is  $\geq 21$ mm, at least 4 times the step size.



This figure shows the interpolated field strength perpendicular to the dipole. The interpolated points follow the raw points with no inconsistencies.

This report shall <u>NOT</u> be reproduced except in full without the written consent of RIM Testing Services Copyright 2005-2009, RIM Testing Services, A division of Research In Motion Limited



The green line in this figure shows the axis along which the points lie.

### Comparison of 5mm and 2mm step sizes

An additional set of measurements was taken: dipole validations were performed using 5mm and 2mm step sizes. The delta between the two readings is insignificant for both field types (< 0.4% for E and 0% for H), demonstrating that 5mm is sufficient. The plots follow.

Testing Services™	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RCP51UW			Page <b>58 (102)</b>
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	Aug 10-20, 2009			

Date/Time: 14/07/2005 11:35:24 AM

Page 1 of 2

Date/Time: 14/07/2005 11:35:24 AM

#### Lab: RIM Testing Services (RTS)

#### Dipole Validation 1880 MHz\_E-Field 07\_14\_05

#### DUT: HAC Dipole 1880 MHz; Type: CD1880V3

Communication System: CW; Frequency: 1880 MHz;Duty Cycle: 1:1 Medium: Air Medium parameters used:  $\sigma = 0$  mho/m,  $\varepsilon_r = 1$ ;  $\rho = 1000$  kg/m<sup>3</sup> Phantom section: H Device Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2285; ConvF(1, 1, 1); Calibrated: 10/12/2004

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/01/2005

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.5 Build 19; Postprocessing SW: SEMCAD, V1.8 Build 146

#### E Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (5x19x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of Total (measured) = 134.8 V/m

E Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (41x181x1): Measurement grid: dx=5mm, dy=5mm Maximum value of Total field (slot averaged) = 131.0 V/m

Hearing Aid Near-Field Category: M2 (AWF 0 dB)

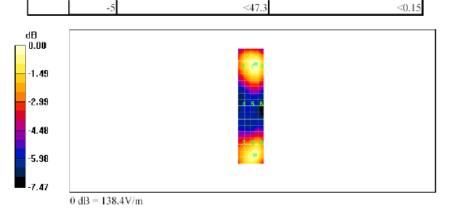
E in V/m (Time averaged) E in V/m (Slot averaged)

Grid 1	Grid 2	Grid 3			Grid 3
123.2	138.1	138.4	123.2	138.1	138.4
Grid 4	Grid 5	Grid 6	Grid 4	Grid 5	Grid 6
80.9	92.3	92.2	80.9	92.3	92.2
Grid 7					Grid 9
119.8	131.0	130.7	119.8	131.0	130.7

Category	AWF (dB)	Limits for E-Field Emissions (V/m)	Limits for H-Field Emissions (A/m)
М1	0	199.5 - 354.8	0.6 - 1.07
	-5	149.6 - 266.1	0.45 - 0.8
M2	0	112.2 - 199.5	0.34 - 0.6
	-5	84.1 - 149.6	0.25 - 0.45
М3	0	63.1 - 112.2	0.19 - 0.34
	-5	47.3 - 84.1	0.15 - 0.25
M4	0	<63.1	<0.19

file://C:\Program%20Files\DASY4\Print\_Templates\Dipole%20Validation%201880%20... 14/07/2005

Testing Services™	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RCP51UW				
Author Data Daoud Attayi	Dates of Test Aug 10-20, 2009	Report No RTS-1765-0908-17	FCC ID L6ARCP50U	JW	
Date/Time: 14/07/2005 11:35:24 AM			Page 2 of 2		



 $file: // C: \label{eq:program} 20 Files \DASY4 \Print\_Templates \Dipole \20 Validation \201880 \20 ... 14/07/2005$ 

This report shall <u>NOT</u> be reproduced except in full without the written consent of RIM Testing Services Copyright 2005-2009, RIM Testing Services, A division of Research In Motion Limited

Testing Services™	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RCP51UW			
Author Data	Dates of Test	Dates of Test Report No FCC ID		
Daoud Attayi	Aug 10-20, 2009			

Date/Time: 14/07/2005 11:44:51 AM

Page 1 of 2

Date/Time: 14/07/2005 11:44:51 AM

#### Lab: RIM Testing Services (RTS)

#### Dipole Validation 1880 MHz\_2mm step\_E-Field 07\_14\_05

#### DUT: HAC Dipole 1880 MHz; Type: CD1880V3

Communication System: CW; Frequency: 1880 MHz;Duty Cycle: 1:1 Medium: Air Medium parameters used:  $\sigma = 0$  mho/m,  $\varepsilon_r = 1$ ;  $\rho = 1000$  kg/m<sup>3</sup> Phantom section: H Device Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2285; ConvF(1, 1, 1); Calibrated: 10/12/2004

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/01/2005

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.5 Build 19; Postprocessing SW: SEMCAD, V1.8 Build 146

#### E Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (11x46x1): Measurement grid: dx=2mm, dy=2mm

Maximum value of Total (measured) = 138.0 V/m

E Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (101x451x1): Measurement grid: dx=2mm, dy=2mm Maximum value of Total field (slot averaged) = 131.2 V/m

Hearing Aid Near-Field Category: M2 (AWF 0 dB)

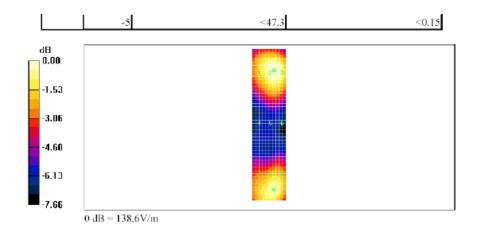
E in V/m (Time averaged) E in V/m (Slot averaged)

Grid 1	Grid 2	Grid 3			Grid 3
123.1	138.6	138.6	123.1	138.6	138.6
Grid 4			Grid 4	Grid 5	Grid 6
81.4	92.1	91.6	81.4	92.1	91.6
Grid 7					Grid 9
121.2	131.2	131.0	121.3	131.2	131.0

Category	AWF (dB)	Limits for E-Field Emissions (V/m)	Limits for H-Field Emissions (A/m)
M1	0	199.5 - 354.8	0.6 - 1.07
	-5	149.6 - 266.1	0.45 - 0.8
M2	0	112.2 - 199.5	0.34 - 0.6
	-5	84.1 - 149.6	0.25 - 0.45
М3	0	63.1 - 112.2	0.19 - 0.34
	-5	47.3 - 84.1	0.15 - 0.25
M4	0	<63.1	<0.19

file://C:\Program%20Files\DASY4\Print\_Templates\Dipole%20Validation%201880%20... 14/07/2005

61 (102)	el RCP51UW	Services**		
	FCC ID	Report No	Dates of Test	Author Data
7	L6ARCP50U	RTS-1765-0908-17	Aug 10-20, 2009	Daoud Attayi
7		1		



file://C:\Program%20Files\DASY4\Print\_Templates\Dipole%20Validation%201880%20... 14/07/2005

This report shall <u>NOT</u> be reproduced except in full without the written consent of RIM Testing Services Copyright 2005-2009, RIM Testing Services, A division of Research In Motion Limited

Testing Services™	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RCP51UW			
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	Aug 10-20, 2009			

Date/Time: 14/07/2005 12:43:02 PM

Page 1 of 2

Date/Time: 14/07/2005 12:43:02 PM

#### Lab: RIM Testing Services (RTS)

### HAC\_H\_Dipole\_CW 1880\_5 mm step\_07\_14\_05

#### DUT: HAC Dipole 1880 MHz; Type: CD1880V3

Communication System: CW; Frequency: 1880 MHz;Duty Cycle: 1:1 Medium: Air Medium parameters used:  $\sigma = 0$  mho/m,  $\varepsilon_r = 1$ ;  $\rho = 1$  kg/m<sup>3</sup> Phantom section: H Dipole Section

DASY4 Configuration:

- Probe: H3DV6 SN6105; ; Calibrated: 10/12/2004
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 03/01/2005
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.5 Build 19; Postprocessing SW: SEMCAD, V1.8 Build 146

#### H Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (5x19x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of Total (measured) = 0.406 A/m

H Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (41x181x1): Measurement grid: dx=5mm, dy=5mm Maximum value of Total field (slot averaged) = 0.406 A/m Hearing Aid Near-Field Category: M2 (AWF 0 dB)

H in A/m (Time averaged) H in A/m (Slot averaged)

Grid 1	Grid 2	Grid 3	Grid 1	Grid 2	Grid 3
0.342	0.359	0.344	0.342	0.359	0.344
Grid 4	Grid 5	Grid 6		Grid 5	
0.389	0.406	0.389	0.389	0.406	0.389
		Grid 9	Grid 7	Grid 8	Grid 9
0.363	0.378	0.363	0.363	0.378	0.363

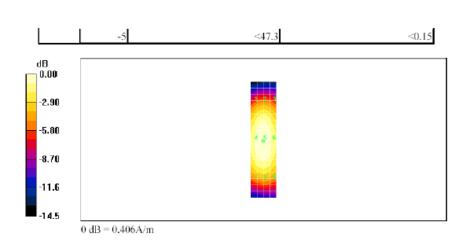
Catego	ry AWF (dB)	Limits for E-Field Emissions (V/m)	Limits for H-Field Emissions (A/m)
М1	0	199.5 - 354.8	0.6 - 1.07
	-5	149.6 - 266.1	0.45 - 0.8
М2	0	112.2 - 199.5	0.34 - 0.6
	-5	84.1 - 149.6	0.25 - 0.45
М3	0	63.1 - 112.2	0.19 - 0.34
	-5	47.3 - 84.1	0.15 - 0.25
M4	0	<63.1	<0.19

file://C:\Program%20Files\DASY4\Print\_Templates\HAC\_H\_Dipole\_CW%201880\_5%... 14/07/2005

Testing Services™	Annex A to Hearing Report for the Black	Page 63 (102)		
Author Data	Dates of Test	Dates of Test Report No FCC ID		
Daoud Attayi	Aug 10-20, 2009	Aug 10-20, 2009 RTS-1765-0908-17 L6ARCP50UW		

Date/Time: 14/07/2005 12:43:02 PM

Page 2 of 2



file://C:\Program%20Files\DASY4\Print\_Templates\HAC\_H\_Dipole\_CW%201880\_5%... 14/07/2005

Testing Services™	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RCP51UW			
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	Aug 10-20, 2009	·I		

Date/Time: 14/07/2005 12:53:40 PM

Page 1 of 2

Date/Time: 14/07/2005 12:53:40 PM

#### Lab: RIM Testing Services (RTS)

#### HAC\_H\_Dipole\_CW 1880\_2 mm step\_07\_14\_05

#### DUT: HAC Dipole 1880 MHz; Type: CD1880V3

Communication System: CW; Frequency: 1880 MHz;Duty Cycle: 1:1 Medium: Air Medium parameters used:  $\sigma = 0$  mho/m,  $\varepsilon_r = 1$ ;  $\rho = 1$  kg/m<sup>3</sup> Phantom section: H Dipole Section

DASY4 Configuration:

- Probe: H3DV6 SN6105; ; Calibrated: 10/12/2004
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 03/01/2005
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.5 Build 19; Postprocessing SW: SEMCAD, V1.8 Build 146

#### H Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (11x46x1): Measurement grid: dx=2mm, dy=2mm

Maximum value of Total (measured) = 0.406 A/m

H Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (101x451x1):

Measurement grid: dx=2mm, dy=2mm Maximum value of Total field (slot averaged) = 0.406 A/m

Hearing Aid Near-Field Category: M2 (AWF 0 dB)

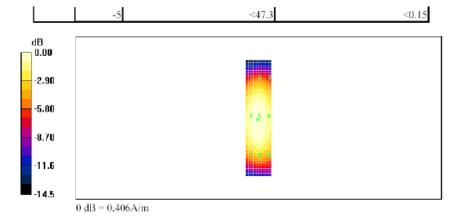
H in A/m (Time averaged) H in A/m (Slot averaged)

Grid 1	Grid 2	Grid 3			Grid 3
0.347	0.361	0.348	0.347	0.361	0.348
Grid 4	Grid 5	Grid 6	Grid 4	Grid 5	Grid 6
0.394	0.406	0.391	0.394	0.406	0.391
Grid 7	Grid 8	Grid 9	Grid 7	Grid 8	Grid 9
0.367	0.380	0.365	0.367	0.380	0.365

Category	(AWF (dB)	Limits for E-Field Emissions (V/m)	Limits for H-Field Emissions (A/m)
М1	0	199.5 - 354.8	0.6 - 1.07
	-5	149.6 - 266.1	0.45 - 0.8
M2	0	112.2 - 199.5	0.34 - 0.6
	-5	84.1 - 149.6	0.25 - 0.45
М3	0	63.1 - 112.2	0.19 - 0.34
	-5	47.3 - 84.1	0.15 - 0.25
M4	0	<63.1	<0.19

file://C:\Program%20Files\DASY4\Print\_Templates\HAC\_H\_Dipole\_CW%201880\_2%... 14/07/2005

Testing Services™	Document Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RCP51UWPage 65 (102)			
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	Aug 10-20, 2009	RTS-1765-0908-17	L6ARCP50U	W
Date/Time: 14/07/2005 12:53:40 PM		Page 2 of 2		



 $file://C: Program\%20Files \ DASY4 \ Print\_Templates \ HAC\_H\_Dipole\_CW\%201880\_2\%... 14/07/2005$ 

This report shall <u>NOT</u> be reproduced except in full without the written consent of RIM Testing Services Copyright 2005-2009, RIM Testing Services, A division of Research In Motion Limited

Testing Services™	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RCP51UW			Page 66 (102)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	Aug 10-20, 2009	RTS-1765-0908-17	L6ARCP50U	W

### A.3 RF emissions plots



Date/Time: 17/08/2009 2:13:33 PM

Test Laboratory: RTS

File Name: <u>HAC\_E\_GSM850\_low\_Chan.da4</u>

## DUT: BlackBerry Smartphone; Type: Sample ; Serial: Not Specified Program Name: HAC RF ER3D Device

Communication System: GSM 850; Frequency: 824.2 MHz; Duty Cycle: 1:8.3

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 1000$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 08/01/2009

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

### E Scan - ER3D - 2007: 15 mm from Probe Center to the

Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 68.8 V/m; Power Drift = -0.070 dB

Maximum value of Total (measured) = 54.2 V/m

## E Scan - ER3D - 2007: 15 mm from Probe Center to the



### Device/Hearing Aid Compatibility Test (101x101x1): Measurement grid:

dx=5mm, dy=5mm

Maximum value of peak Total field = 158.0 V/m

Probe Modulation Factor = 2.91

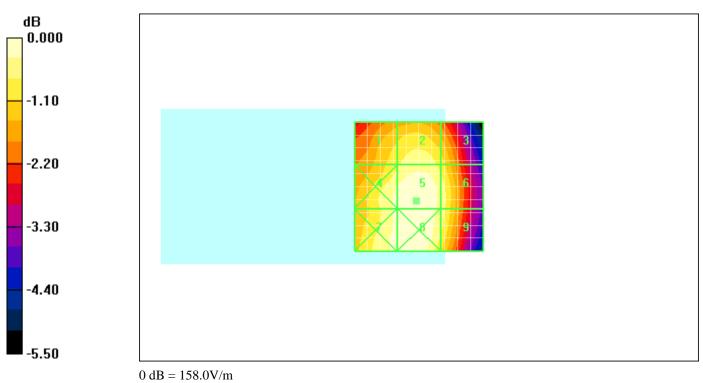
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 68.8 V/m; Power Drift = -0.070 dB

Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Peak E-field in	n V/m	_
Grid 1	Grid 2	Grid 3
144.2	149.8	142.7
Μ	Μ	Μ
4	3	4
Grid 4	Grid 5	Grid 6
153.3	158.0	149.7
Μ	Μ	Μ
3	3	3
Grid 7	Grid 8	Grid 9
154.2	157.3	<b>148.8</b>
Μ	Μ	Μ
3	3	4







Date/Time: 17/08/2009 2:44:55 PM

Test Laboratory: RTS

File Name: <u>HAC\_E\_GSM850\_mid\_Chan.da4</u>

## DUT: BlackBerry Smartphone; Type: Sample ; Serial: Not Specified Program Name: HAC RF ER3D Device

Communication System: GSM 850; Frequency: 836.8 MHz; Duty Cycle: 1:8.3

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 1000$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 08/01/2009

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

### E Scan - ER3D - 2007: 15 mm from Probe Center to the

Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 84.8 V/m; Power Drift = 0.006 dB

Maximum value of Total (measured) = 67.5 V/m

## E Scan - ER3D - 2007: 15 mm from Probe Center to the



### Device/Hearing Aid Compatibility Test (101x101x1): Measurement grid:

dx=5mm, dy=5mm

Maximum value of peak Total field = 195.7 V/m

Probe Modulation Factor = 2.91

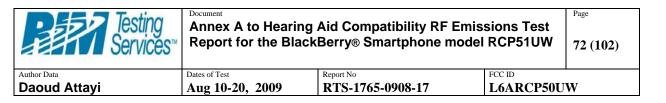
Device Reference Point: 0.000, 0.000, -6.30 mm

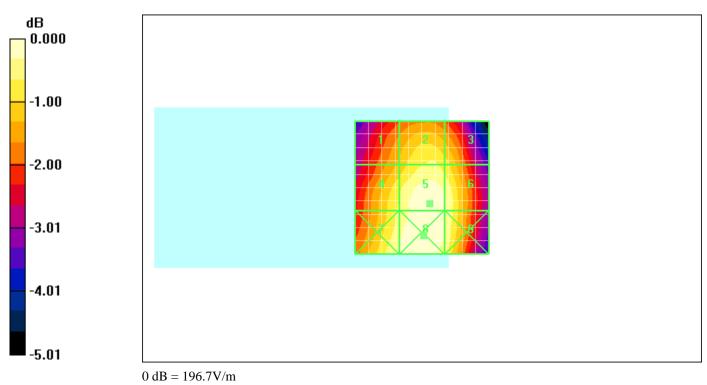
Reference Value = 84.8 V/m; Power Drift = 0.006 dB

Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Peak E-field in V/m

Grid 1	Grid 2	Grid 3
170.8 M3	183.6 M3	179.2 M3
Grid 4	Grid 5	Grid 6
183.7 M3	195.7 M3	190.9 M3
Grid 7	Grid 8	Grid 9
191.3 M3	196.7 M3	190.3 M3







Date/Time: 17/08/2009 2:57:13 PM

Test Laboratory: RTS

File Name: <u>HAC\_E\_GSM850\_high\_Chan.da4</u>

# DUT: BlackBerry Smartphone; Type: Sample ; Serial: Not Specified Program Name: HAC RF ER3D Device

Communication System: GSM 850; Frequency: 848.8 MHz; Duty Cycle: 1:8.3

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 1000$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 08/01/2009

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

### E Scan - ER3D - 2007: 15 mm from Probe Center to the

Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 83.1 V/m; Power Drift = 0.013 dB

Maximum value of Total (measured) = 66.5 V/m



dx=5mm, dy=5mm

Maximum value of peak Total field = 193.9 V/m

Probe Modulation Factor = 2.91

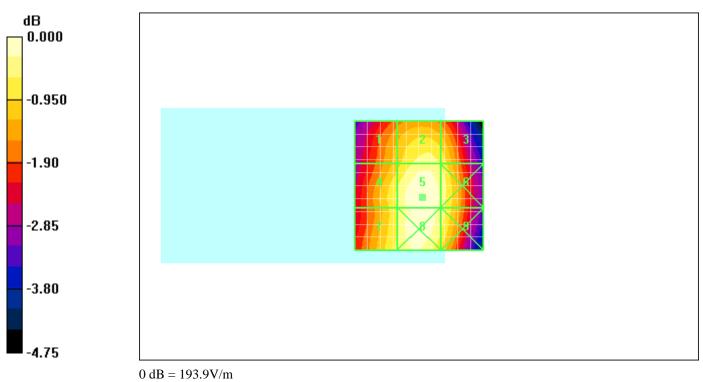
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 83.1 V/m; Power Drift = 0.013 dB

Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Grid 1	Grid 2	Grid 3
171.7 M3	184.5 M3	179.6 M3
Grid 4	Grid 5	Grid 6
181.5 M3	193.9 M3	185.4 M3
Grid 7	Grid 8	Grid 9
181.8 M3	192.2 M3	184.3 M3







Date/Time: 17/08/2009 3:05:06 PM

Test Laboratory: RTS

File Name: HAC\_E\_GSM1900\_Low\_Chan.da4

# DUT: BlackBerry Smartphone; Type: Sample ; Serial: Not Specified Program Name: HAC RF ER3D Device

Communication System: GSM 1900; Frequency: 1850.2 MHz; Duty Cycle: 1:8.3

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 1000$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 08/01/2009

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

### E Scan - ER3D - 2007: 15 mm from Probe Center to the

Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 10.6 V/m; Power Drift = 0.296 dB

Maximum value of Total (measured) = 26.0 V/m



dx=5mm, dy=5mm

Maximum value of peak Total field = 53.7 V/m

Probe Modulation Factor = 2.88

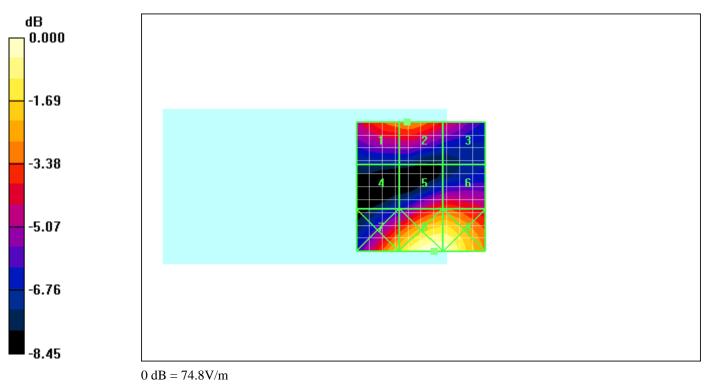
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 10.6 V/m; Power Drift = 0.296 dB

Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Grid 1	Grid 2	Grid 3
53.3 M3	53.7 M3	46.7 M4
Grid 4	Grid 5	Grid 6
35.9 M4	49.6 M3	50.0 M3
Grid 7	Grid 8	Grid 9
61.9 M3	74.8 M3	73.6 M3







Date/Time: 17/08/2009 3:13:00 PM

Test Laboratory: RTS

File Name: HAC\_E\_GSM1900\_Mid\_Chan.da4

# DUT: BlackBerry Smartphone; Type: Sample ; Serial: Not Specified Program Name: HAC RF ER3D Device

Communication System: GSM 1900; Frequency: 1880 MHz; Duty Cycle: 1:8.3

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 1000$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 08/01/2009

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

### E Scan - ER3D - 2007: 15 mm from Probe Center to the

Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 10.3 V/m; Power Drift = 0.182 dB

Maximum value of Total (measured) = 22.1 V/m



dx=5mm, dy=5mm

Maximum value of peak Total field = 43.8 V/m

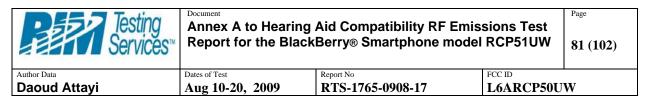
Probe Modulation Factor = 2.88

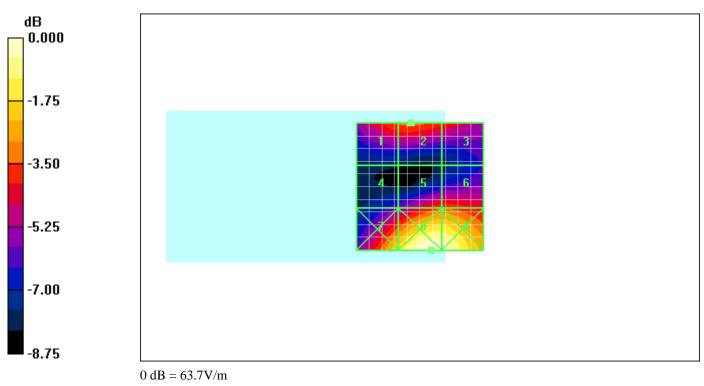
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 10.3 V/m; Power Drift = 0.182 dB

Hearing Aid Near-Field Category: M4 (AWF -5 dB)

Grid 1	Grid 2	Grid 3
43.0 M4	43.8 M4	40.9 M4
Grid 4	Grid 5	Grid 6
32.9 M4	42.4 M4	42.5 M4
Grid 7	Grid 8	Grid 9







Date/Time: 17/08/2009 3:19:50 PM

Test Laboratory: RTS

File Name: <u>HAC\_E\_GSM1900\_High\_Chan.da4</u>

# DUT: BlackBerry Smartphone; Type: Sample ; Serial: Not Specified Program Name: HAC RF ER3D Device

Communication System: GSM 1900; Frequency: 1909.8 MHz; Duty Cycle: 1:8.3

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 1000$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 08/01/2009

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

### E Scan - ER3D - 2007: 15 mm from Probe Center to the

Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 9.66 V/m; Power Drift = 0.119 dB

Maximum value of Total (measured) = 19.0 V/m



dx=5mm, dy=5mm

Maximum value of peak Total field = 40.4 V/m

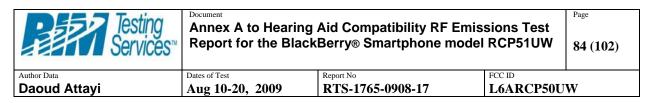
Probe Modulation Factor = 2.88

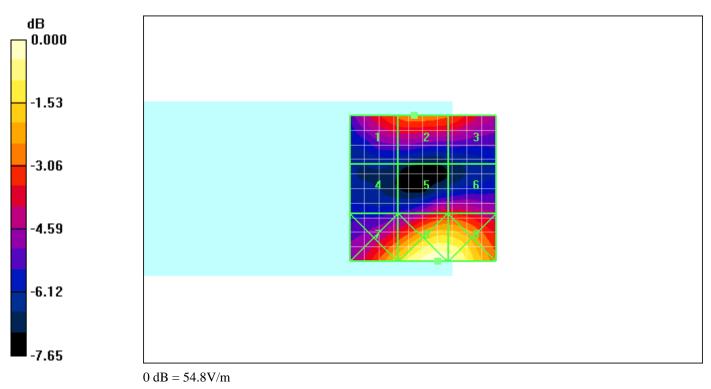
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 9.66 V/m; Power Drift = 0.119 dB

Hearing Aid Near-Field Category: M4 (AWF -5 dB)

Grid 2 Grid 1 Grid 3 39.1 M4 40.4 M4 38.9 M4 Grid 4 Grid 6 Grid 5 29.4 M4 35.9 M4 35.9 M4 Grid 7 Grid 8 Grid 9 46.0 M4 54.8 M3 53.8 M3







Date/Time: 20/08/2009 10:09:46 AM

Test Laboratory: RTS

File Name: <u>HAC\_H\_GSM850\_Low\_Chan.da4</u>

# DUT: BlackBerry Smartphone; Type: Sample ; Serial: Not Specified Program Name: HAC RF H3DV6 Device

Communication System: GSM 850; Frequency: 824.2 MHz; Duty Cycle: 1:8.3

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 1$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY4 Configuration:

- Probe: H3DV6 - SN6168; ; Calibrated: 03/03/2009

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

### H Scan - H3DV6 - 2007: 15 mm from Probe Center to the

Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.063 A/m; Power Drift = 0.035 dB

Maximum value of Total (measured) = 0.114 A/m



dx=5mm, dy=5mm

Maximum value of peak Total field = 0.302 A/m

Probe Modulation Factor = 2.66

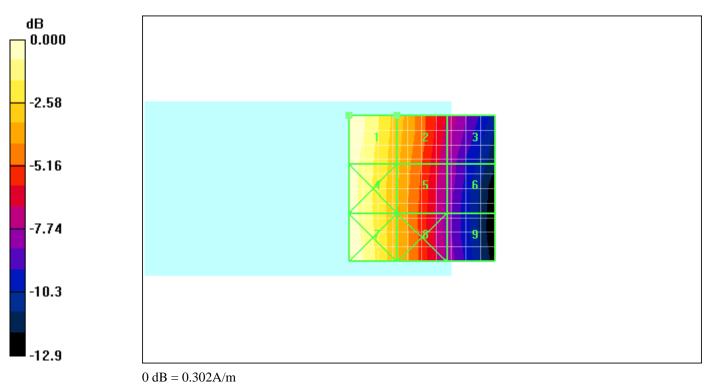
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.063 A/m; Power Drift = 0.035 dB

Hearing Aid Near-Field Category: M4 (AWF -5 dB)

Grid 1	Grid 2	Grid 3
0.302 M4	0.214 M4	0.137 M4
Grid 4	Grid 5	Grid 6
0.292 M4	0.208 M4	0.126 M4
Grid 7	Grid 8	Grid 9
0.300 M4	0.207 M4	0.121 M4







Date/Time: 20/08/2009 10:17:20 AM

Test Laboratory: RTS

File Name: <u>HAC\_H\_GSM850\_Mid\_Chan.da4</u>

# DUT: BlackBerry Smartphone; Type: Sample ; Serial: Not Specified Program Name: HAC RF H3DV6 Device

Communication System: GSM 850; Frequency: 824.2 MHz; Duty Cycle: 1:8.3

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 1$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY4 Configuration:

- Probe: H3DV6 - SN6168; ; Calibrated: 03/03/2009

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

### H Scan - H3DV6 - 2007: 15 mm from Probe Center to the

Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.075 A/m; Power Drift = -0.059 dB

Maximum value of Total (measured) = 0.136 A/m



dx=5mm, dy=5mm

Maximum value of peak Total field = 0.355 A/m

Probe Modulation Factor = 2.66

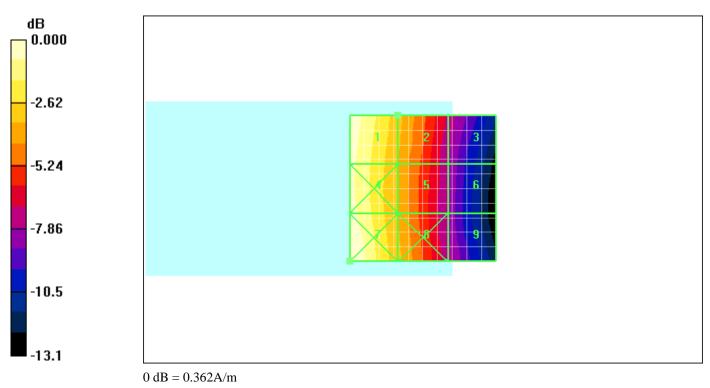
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.075 A/m; Power Drift = -0.059 dB

Hearing Aid Near-Field Category: M4 (AWF -5 dB)

Grid 1	Grid 2	Grid 3
0.355 M4	0.252 M4	0.159 M4
Grid 4	Grid 5	Grid 6
0.339 M4	0.241 M4	0.149 M4
Grid 7	Grid 8	Grid 9
0.362 M4	0.249 M4	0.153 M4







Date/Time: 20/08/2009 10:23:20 AM

Test Laboratory: RTS

File Name: HAC\_H\_GSM850\_High\_Chan.da4

# DUT: BlackBerry Smartphone; Type: Sample ; Serial: Not Specified Program Name: HAC RF H3DV6 Device

Communication System: GSM 850; Frequency: 848.8 MHz; Duty Cycle: 1:8.3

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 1$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY4 Configuration:

- Probe: H3DV6 - SN6168; ; Calibrated: 03/03/2009

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

### H Scan - H3DV6 - 2007: 15 mm from Probe Center to the

Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.090 A/m; Power Drift = -0.069 dB

Maximum value of Total (measured) = 0.154 A/m



dx=5mm, dy=5mm

Maximum value of peak Total field = 0.387 A/m

Probe Modulation Factor = 2.66

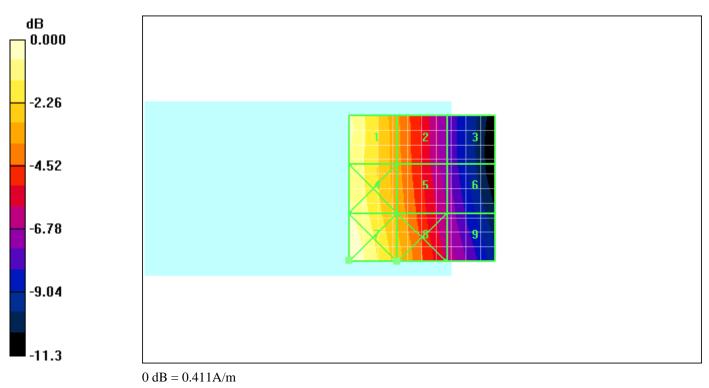
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.090 A/m; Power Drift = -0.069 dB

Hearing Aid Near-Field Category: M4 (AWF -5 dB)

Grid 1	Grid 2	Grid 3
0.387 M4	0.275 M4	0.177 M4
Grid 4	Grid 5	Grid 6
0.385 M4	0.285 M4	0.187 M4
Grid 7	Grid 8	Grid 9
0.411 M4	0.303 M4	0.203 M4







Date/Time: 20/08/2009 10:29:15 AM

Test Laboratory: RTS

File Name: <u>HAC\_H\_GSM1900\_Low\_Chan.da4</u>

# DUT: BlackBerry Smartphone; Type: Sample ; Serial: Not Specified Program Name: HAC RF H3DV6 Device

Communication System: GSM 1900; Frequency: 1850.2 MHz; Duty Cycle: 1:8.3

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 1$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY4 Configuration:

- Probe: H3DV6 - SN6168; ; Calibrated: 03/03/2009

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

### H Scan - H3DV6 - 2007: 15 mm from Probe Center to the

Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.063 A/m; Power Drift = 0.220 dB

Maximum value of Total (measured) = 0.068 A/m



dx=5mm, dy=5mm

Maximum value of peak Total field = 0.126 A/m

Probe Modulation Factor = 2.25

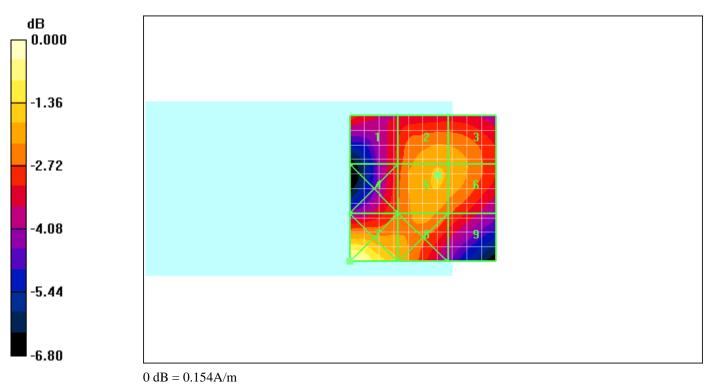
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.063 A/m; Power Drift = 0.220 dB

Hearing Aid Near-Field Category: M4 (AWF -5 dB)

Grid 1	Grid 2	Grid 3
0.111 M4	0.124 M4	0.123 M4
Grid 4	Grid 5	Grid 6
0.114 M4	0.126 M4	0.124 M4
Grid 7	Grid 8	Grid 9
0.154 M3	0.125 M4	0.114 M4







Date/Time: 20/08/2009 10:37:31 AM

Test Laboratory: RTS

File Name: HAC\_H\_GSM1900\_Mid\_Chan.da4

# DUT: BlackBerry Smartphone; Type: Sample ; Serial: Not Specified Program Name: HAC RF H3DV6 Device

Communication System: GSM 1900; Frequency: 1880 MHz; Duty Cycle: 1:8.3

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 1$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY4 Configuration:

- Probe: H3DV6 - SN6168; ; Calibrated: 03/03/2009

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

### H Scan - H3DV6 - 2007: 15 mm from Probe Center to the

Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.059 A/m; Power Drift = -0.094 dB

Maximum value of Total (measured) = 0.061 A/m



dx=5mm, dy=5mm

Maximum value of peak Total field = 0.113 A/m

Probe Modulation Factor = 2.25

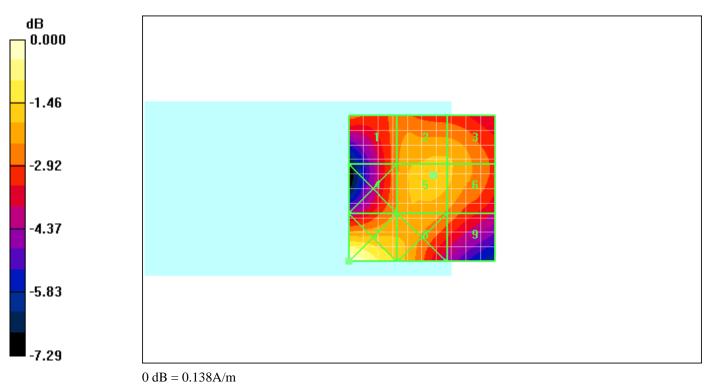
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.059 A/m; Power Drift = -0.094 dB

Hearing Aid Near-Field Category: M4 (AWF -5 dB)

Grid 1	Grid 2	Grid 3
0.103 M4	0.112 M4	0.112 M4
Grid 4	Grid 5	Grid 6
0.106 M4	0.113 M4	0.112 M4
Grid 7	Grid 8	Grid 9
0.138 M4	0.114 M4	0.103 M4







Date/Time: 20/08/2009 10:43:59 AM

Test Laboratory: RTS

File Name: <u>HAC\_H\_GSM1900\_High\_Chan.da4</u>

# DUT: BlackBerry Smartphone; Type: Sample ; Serial: Not Specified Program Name: HAC RF H3DV6 Device

Communication System: GSM 1900; Frequency: 1909.8 MHz; Duty Cycle: 1:8.3

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 1$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY4 Configuration:

- Probe: H3DV6 - SN6168; ; Calibrated: 03/03/2009

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

### H Scan - H3DV6 - 2007: 15 mm from Probe Center to the

Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.051 A/m; Power Drift = 0.122 dB

Maximum value of Total (measured) = 0.056 A/m



dx=5mm, dy=5mm

Maximum value of peak Total field = 0.101 A/m

Probe Modulation Factor = 2.25

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.051 A/m; Power Drift = 0.122 dB

Hearing Aid Near-Field Category: M4 (AWF -5 dB)

0.100 M4
Grid 6
0.101 M4
Grid 9
0.093 M4



